Silicon NPN Power Transistors 2SC3636

DESCRIPTION

- With TO-3PN package
- High voltage ,high speed
- High reliability

APPLICATIONS

- Ultrahigh-definition CRT display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

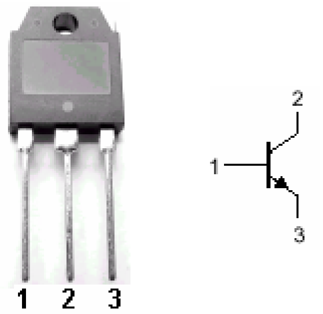

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	900	V
V_{CEO}	Collector-emitter voltage	Open base	500	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		14	A
P_C	Collector power dissipation	T_C=25□	80	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ; I_B=0	500			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A ;I_B=0.8A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A ;I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=500V; I_E=0			10	μA
I_{CES}	Collector cut-off current	V_{CE}=900V; R_{BE}=0			0.5	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			1.0	mA
h_{FE}	DC current gain	I_C=0.8A ; V_{CE}=5V	8			
Switching times						
t_s	Storage time	V_{CC}=200V;I_C=4A; I_{B1}=0.8A; I_{B2}=-1.6A			3.0	μs
t_f	Fall time			0.1	0.2	μs

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PACKAGE OUTLINE

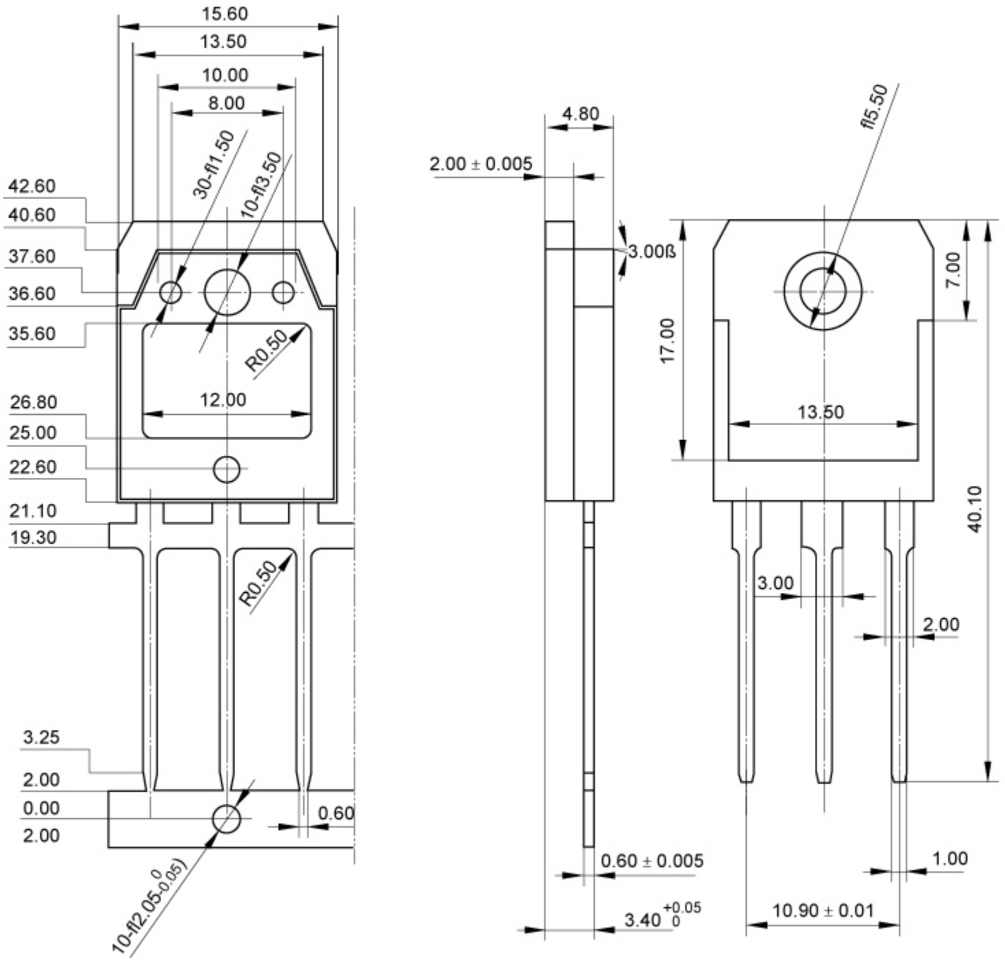

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

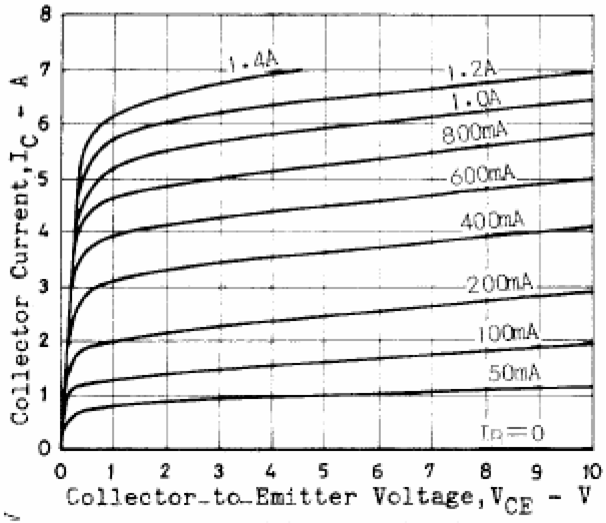

Fig.3 Static Characteristic

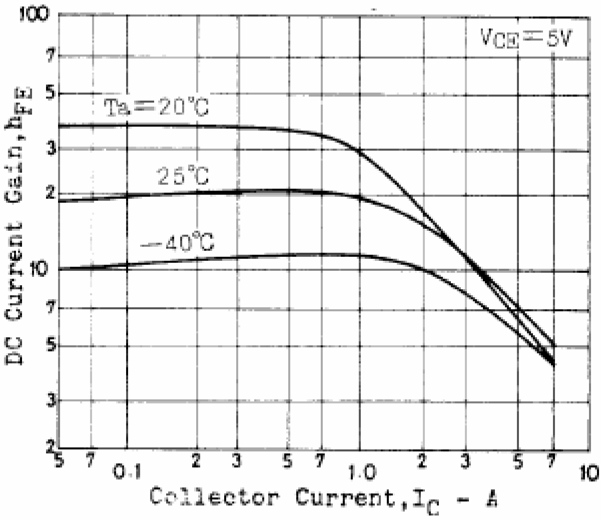

Fig.4 DC current Gain

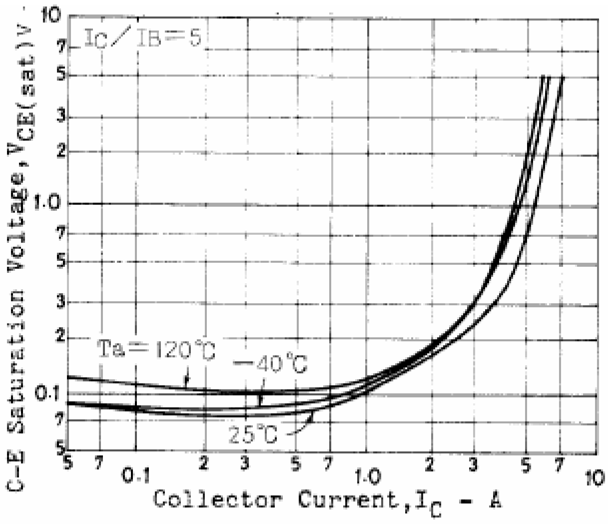

Fig.5 Collector-Emitter Saturation Voltage

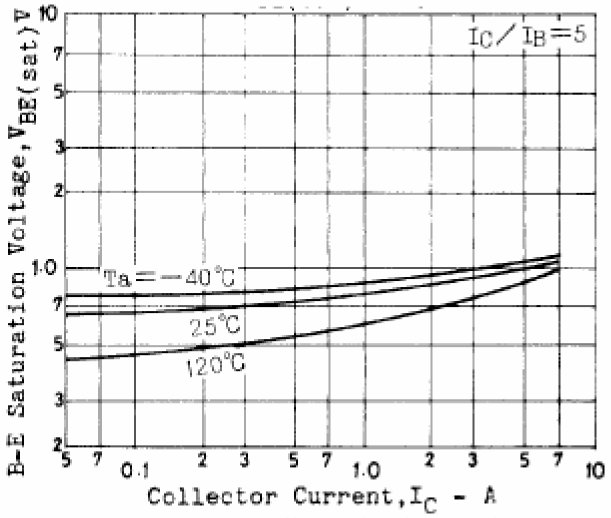

Fig.6 Base-Emitter Saturation Voltage

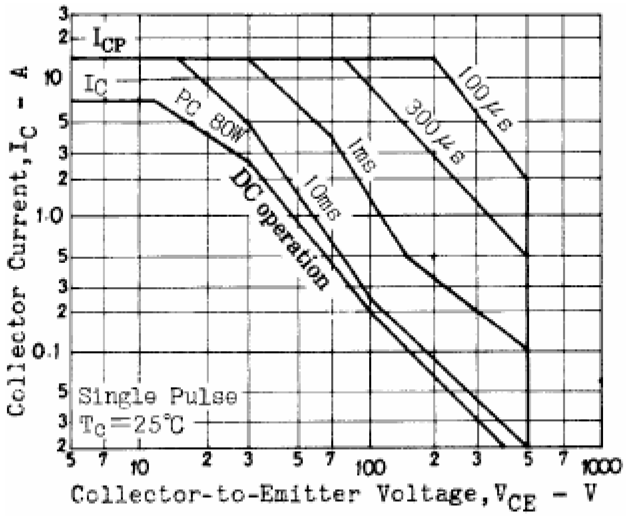

Fig.7 Safe Operating Area